

### **TSM4415**

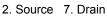
### 30V P-Channel MOSFET



SOP-8

#### Pin Definition:

1. Source 8. Drain



3. Source 6. Drain

4. Gate 5. Drain

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
-30	26 @ V <sub>GS</sub> = -20V	-8.0
	35 @ V <sub>GS</sub> = -10V	-8.0

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

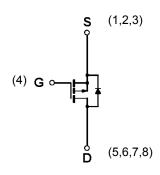
#### **Application**

- Load Switch
- PA Switch

#### **Ordering Information**

Part No.	Package	Packing
TSM4415CS RL	SOP-8	2.5kpcs/13" reel

### **Block Diagram**



P-Channel MOSFET

### Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	-30	V	
Gate-Source Voltage		$V_{GS}$	±25	V	
Continuous Drain Current, V <sub>GS</sub> @4.5V.		I <sub>D</sub>	-8	Α	
Pulsed Drain Current, V <sub>GS</sub> @4.5V		I <sub>DM</sub>	-30	Α	
Continuous Source Current (Diode Con	duction) <sup>a,b</sup>	I <sub>S</sub>	-1	Α	
Maying Payer Discination	Ta = 25 °C	Б	3	W	
Maximum Power Dissipation	Ta = 70°C	P <sub>D</sub>	2.1		
Operating Junction Temperature		T <sub>J</sub>	+150	°C	
Operating Junction and Storage Temper	erature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖ <sub>JF</sub>	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ <sub>JA</sub>	75	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.

1/1 Version: Preliminary



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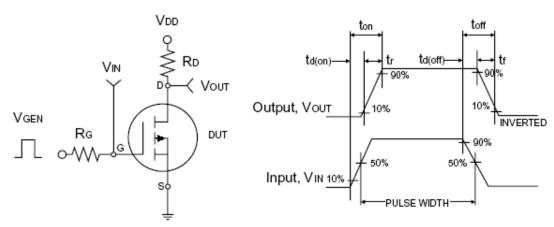


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV <sub>DSS</sub>	-30		-	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.0		-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I <sub>DSS</sub>	-		-1.0	μΑ
On-State Drain Current <sup>a</sup>	V <sub>DS</sub> ≥-10V, V <sub>GS</sub> = -5V	$I_{D(ON)}$	-6		-	Α
	$V_{GS} = -20V, I_{D} = -8A$		-	21	26	
Drain-Source On-State Resistance	$V_{GS} = -10V, I_{D} = -8A$	R <sub>DS(ON)</sub>		28	35	mΩ
	$V_{GS} = -6V, I_{D} = -5A$		-	41	-	
Forward Transconductance <sup>a</sup>	$V_{DS} = -5V, I_{D} = -8A$	g <sub>fs</sub>	-	11.5	-	S
Diode Forward Voltage	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	$V_{SD}$	1	-0.8	-1.0	V
Dynamic <sup>b</sup>						
Total Gate Charge	\/ - 15\/   - 01	$Q_g$		18.1		
Gate-Source Charge	$V_{DS} = V_{GS}, I_D = -250 \mu A$ $V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{DS} = -24V, V_{GS} = 0V$ $V_{DS} \ge -10V, V_{GS} = -5V$ $V_{GS} = -20V, I_D = -8A$ $V_{GS} = -10V, I_D = -8A$ $V_{GS} = -6V, I_D = -5A$ $V_{DS} = -5V, I_D = -8A$	$Q_gs$		6.5		nC
Gate-Drain Charge	V <sub>GS</sub> = -10V	$Q_{gd}$		3.2	-	
Input Capacitance	\/ - 15\/ \/ - 0\/	$C_{iss}$		1047.9	-	
Output Capacitance	, 66 ,	C <sub>oss</sub>	1	172.8	I	pF
Reverse Transfer Capacitance	1 = 1.0IVIDZ	C <sub>rss</sub>		115.5		
Switching <sup>c</sup>						
Turn-On Delay Time	15) / D 100	t <sub>d(on)</sub>		20.5		
Turn-On Rise Time		t <sub>r</sub>		4.4		20
Turn-Off Delay Time	, 52.1	t <sub>d(off)</sub>		42.8		nS
Turn-Off Fall Time	11G - 322	t <sub>f</sub>		7.3		

#### Notes:

- a. pulse test: PW ≤300μS, duty cycle ≤2%
  b. For DESIGN AID ONLY, not subject to production testing.
  b. Switching time is essentially independent of operating temperature.



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**Switching Test Circuit** 

Switchin Waveforms

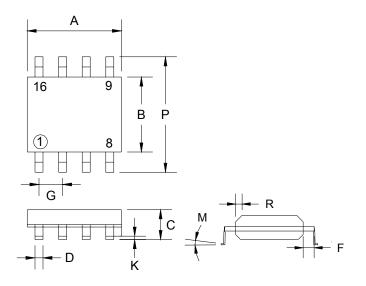


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# **SOP-8 Mechanical Drawing**



SOP-8 DIMENSION						
DIM	MILLIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX.		
Α	4.80	5.00	0.189	0.196		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	1.27BSC		0.05BSC		
K	0.10	0.25	0.004	0.009		
М	0°	7°	0°	7°		
Р	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		



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